



Model 308-SF-02 series Bare Die (Flip chip form, AuSn Pad)

Typical Optical-Electrical Characteristics

 $(I_{F}=20mA, T_{a}=25^{\circ}C)$

ltem	Symbol	Unit	308-SF-02-C		
			Min	Тур	Max
Peak Wavelength	λ _p	nm	303	308	313
Radiant Flux	Po	mW	-	4.8	-
Full Width at Half Maximum	⊿λ	nm	-	15	-
Forward Voltage	V _F	V	-	5.0	-

$(I_{F}=50 \text{mA}, T_{a}=25^{\circ}\text{C})$

ltem	Symbol	Unit	308-SF-02-C		
			Min	Тур	Max
Peak Wavelength	λ _p	nm	303	308	313
Radiant Flux	Po	mW	-	12	-
Full Width at Half Maximum	⊿λ	nm	-	15	-
Forward Voltage	V _F	V	-	5.6	-

(*)Peak Wavelength Measurement tolerance is ±3nm.

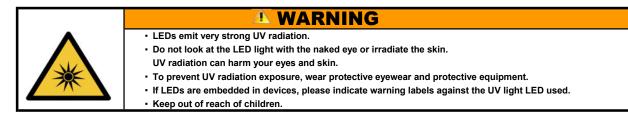
(**)Radiant Flux Measurement tolerance is ±10%.

Binning is available.

Specification and dimension are subject to change for improvement without notice.

Absolute Maximum Ratings

ltem	Symbol	Unit	Value
Forward Current	IF	mΑ	50
Junction Temperature	T_{J}	°C	90
Operating Temperature	T _{OPR}	°C	-30 ~ +85
Storage Temperature	T _{STR}	°C	-40 \sim +85 (No condensation)

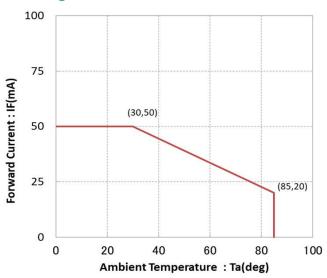






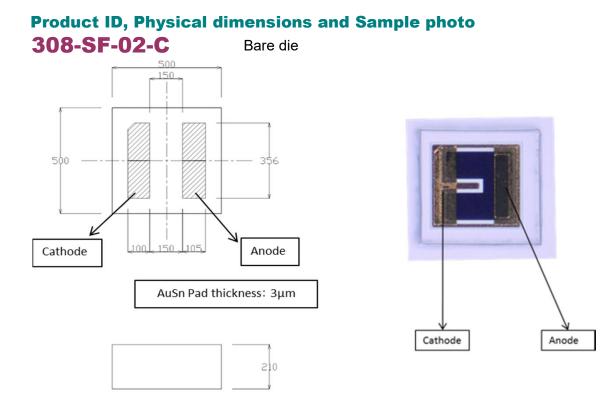
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Derating Curve



Notes:

Maximum ratings and derating curve strongly depend on assembly materials. The above ratings and derating curve were determined using AIN submount ,AI substrate and heatsink. Ratings may be different for other materials and environment.

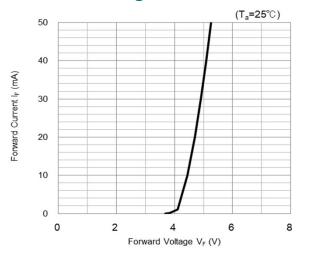




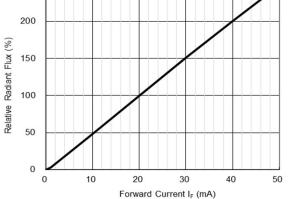
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Reference Data(1)

Forward Voltage vs Forward Current



Forward Current vs Radiated Flux ²⁵⁰ (T_a=25°C)



Spectrum

